
Poster Presentation

[FMCp5]Materials &Components

Thu. Nov 28, 2019 2:30 PM - 5:00 PM Main Hall (1F)

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[FMCp5-8L]Capacitance-Voltage Characteristics of Solution-Based HfZr-Silicate Gate Dielectrics

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In this study, $\text{Al}/(\text{HfZrO}_4)_{1-x}(\text{SiO}_2)_x/\text{p-Si}$ capacitors were fabricated and evaluated as a function of SiO_2 content in the films. From the result, electrical properties enhanced such as oxide charge and breakdown voltage as the SiO_2 concentration x increased and reliability improved as well.